



Electrical Characteristics of the IGBT

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						



Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25						
Dynamic , at T_j= 125						
Dynamic , at T_j= 150						
					n)j



Electrical Characteristics of the Diode

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25						
Dynamic , at T_j= 125						
Dynamic , at T_j= 150						

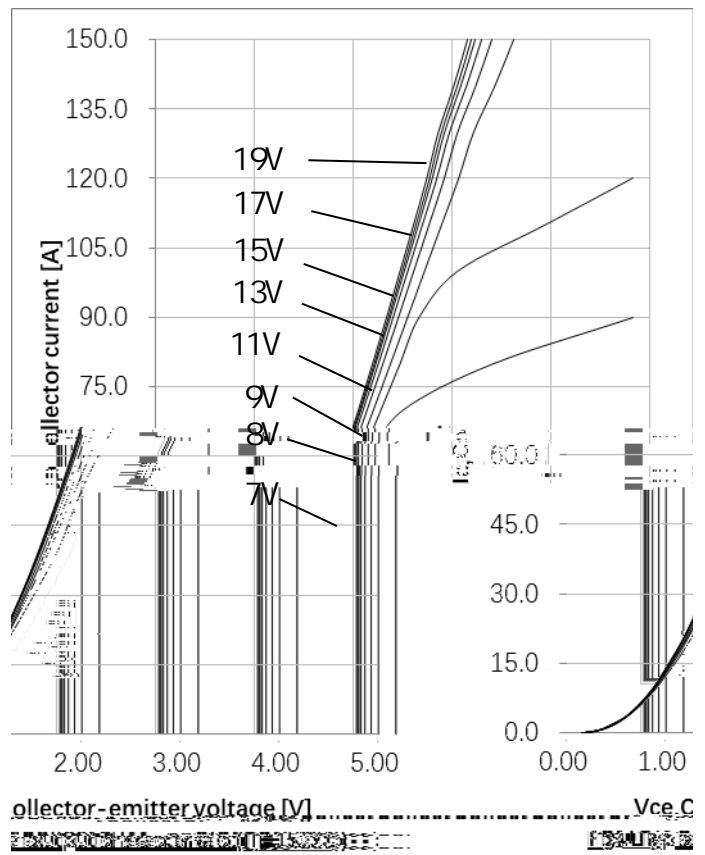
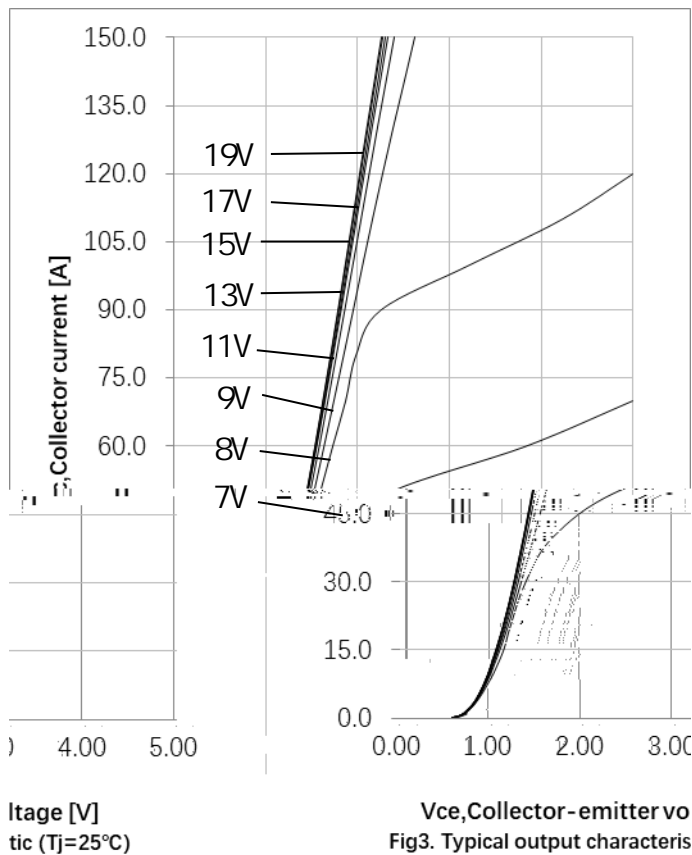
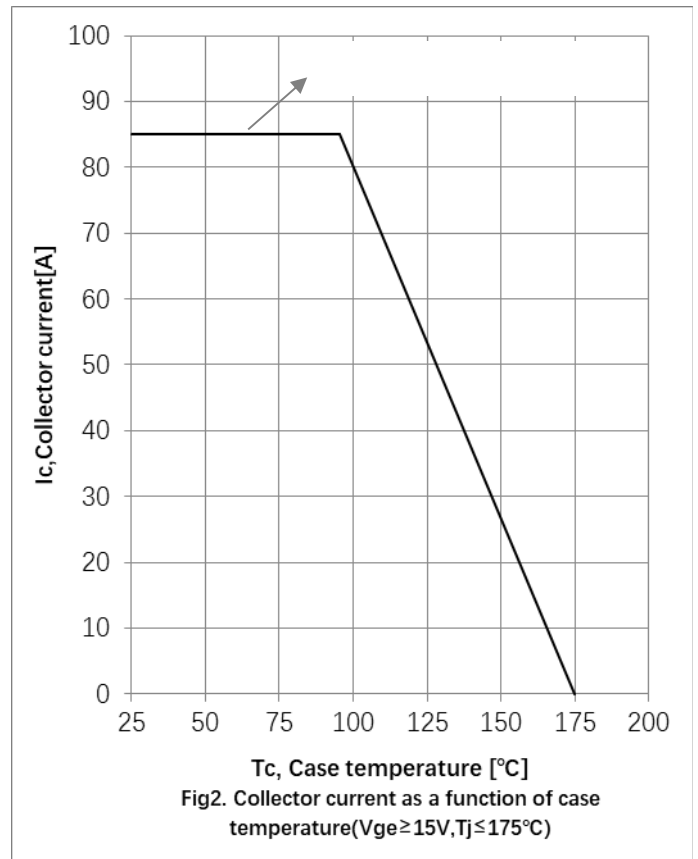
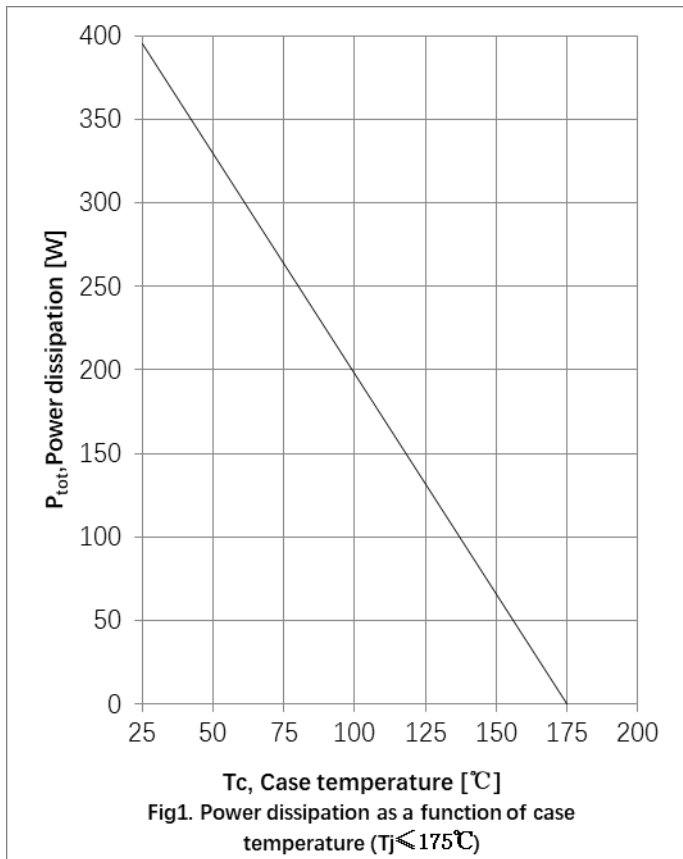
Thermal Resistance

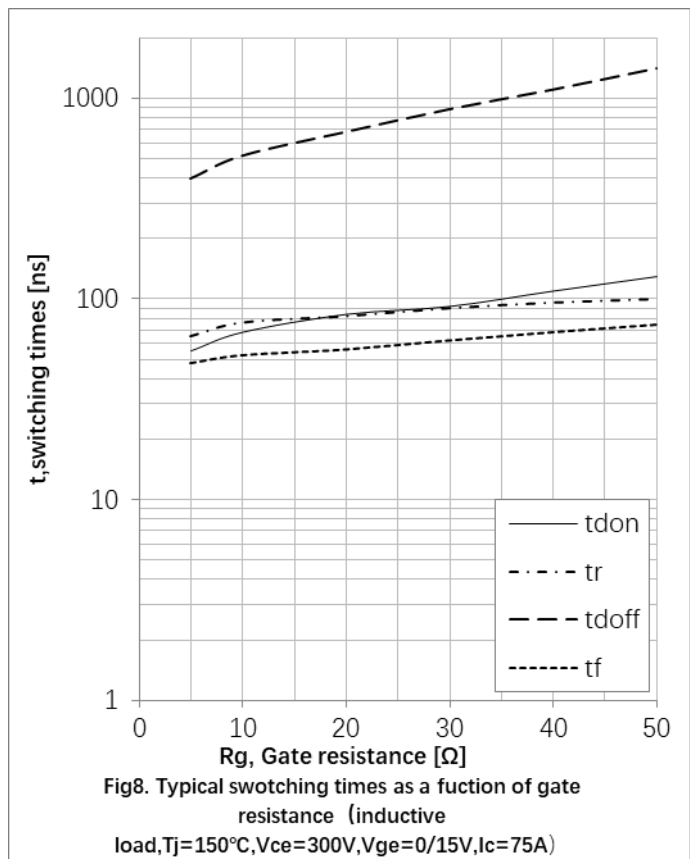
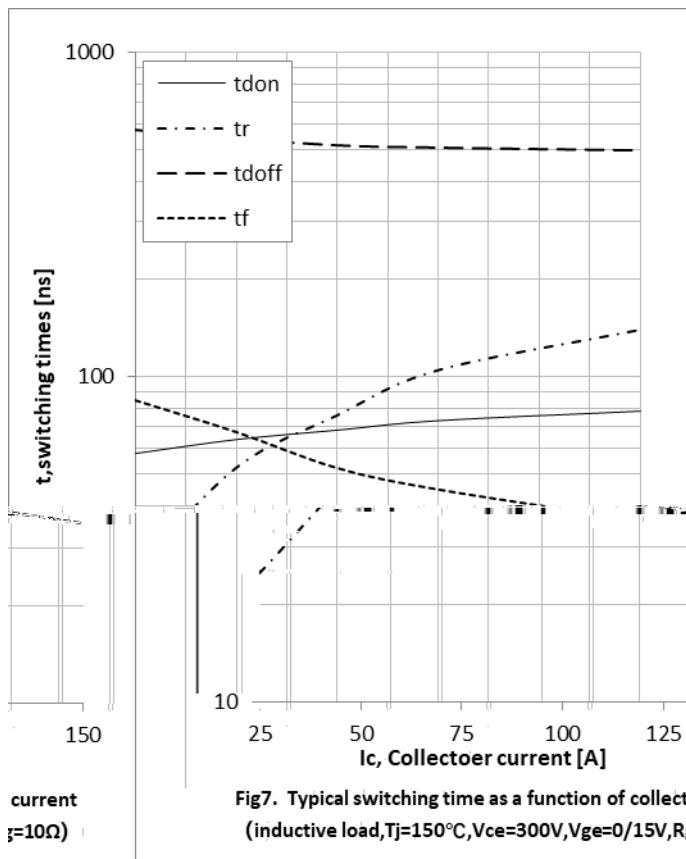
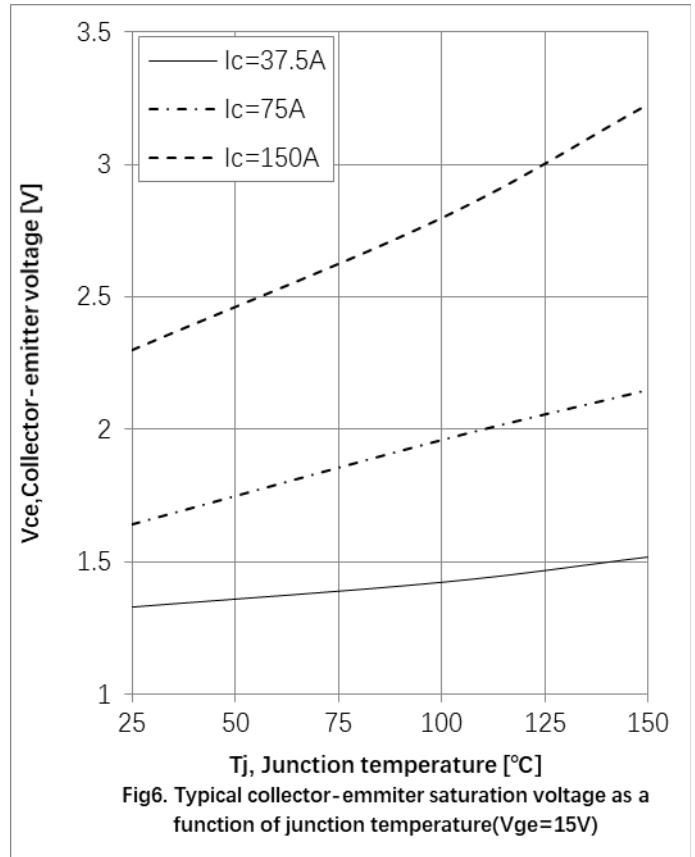
Parameter	Symbol	Max. Value	Unit

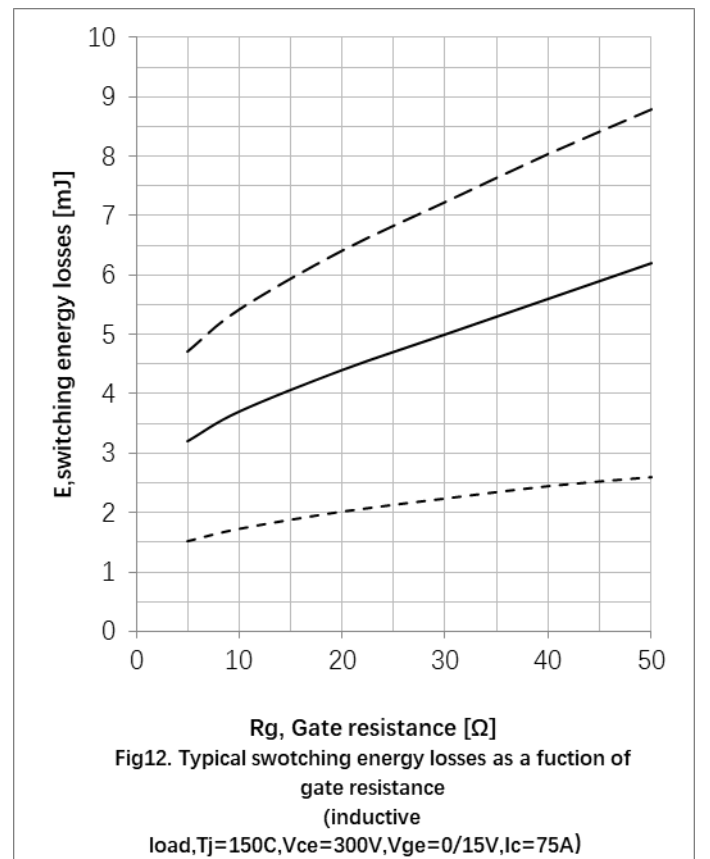
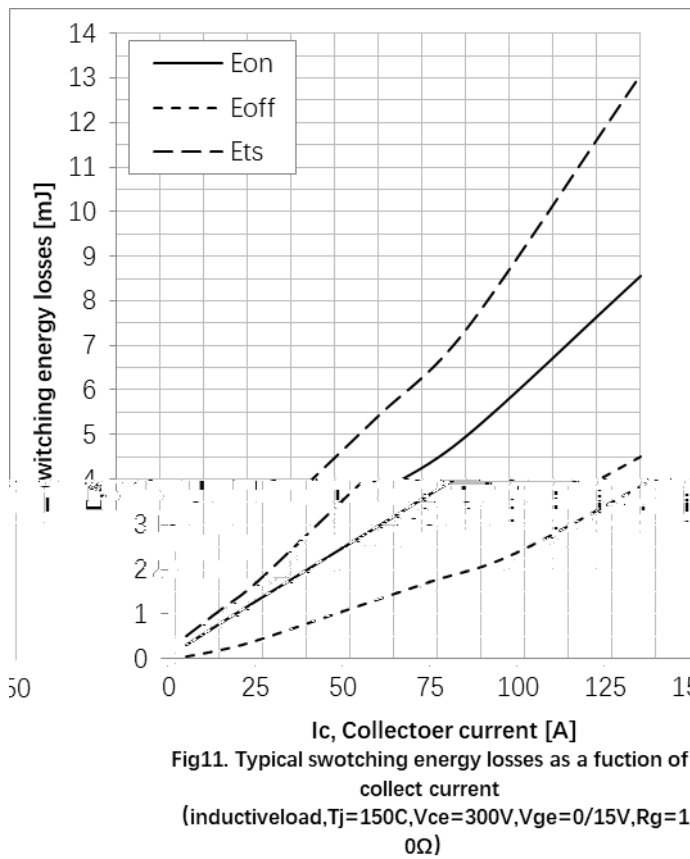
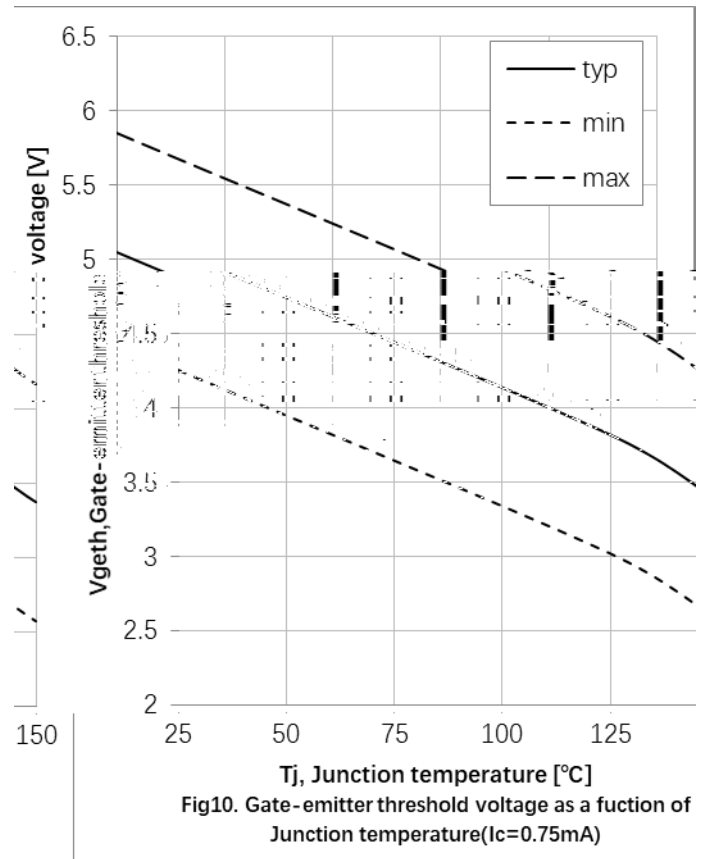
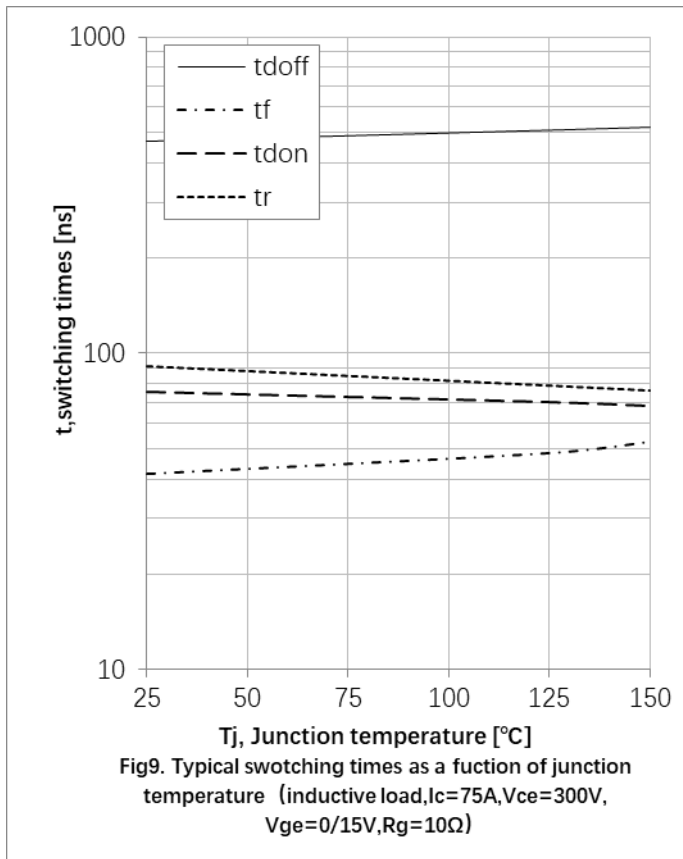


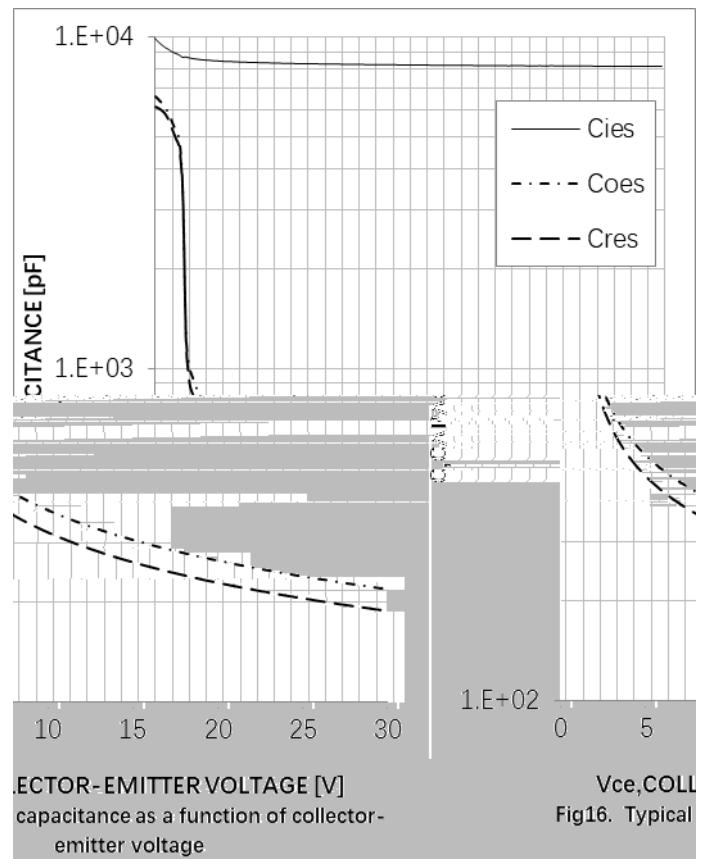
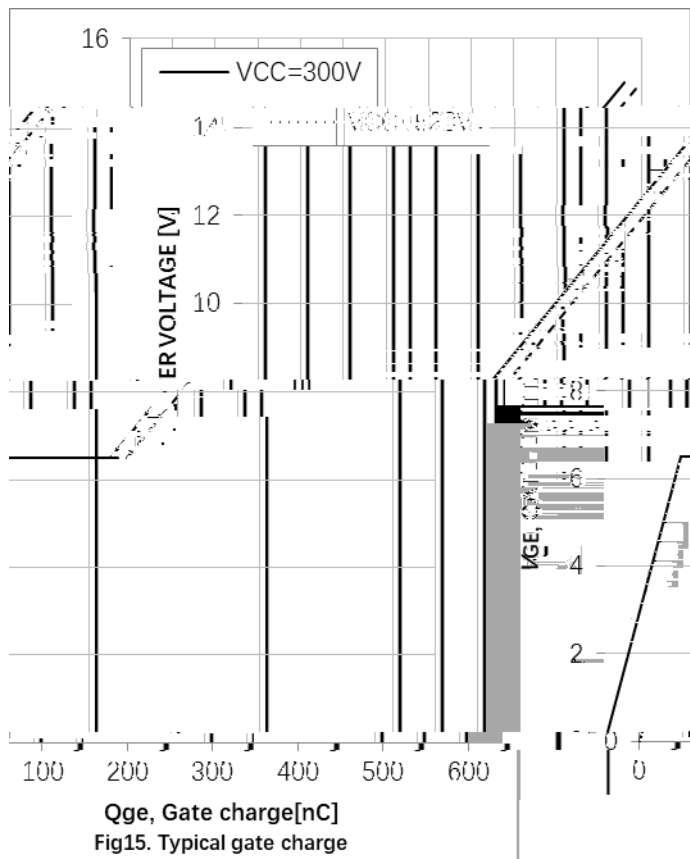
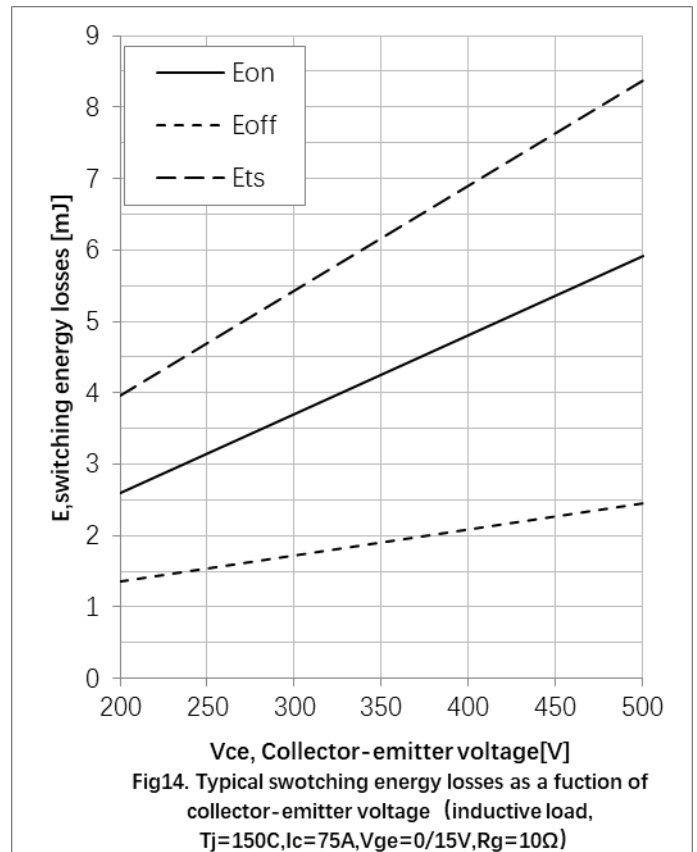
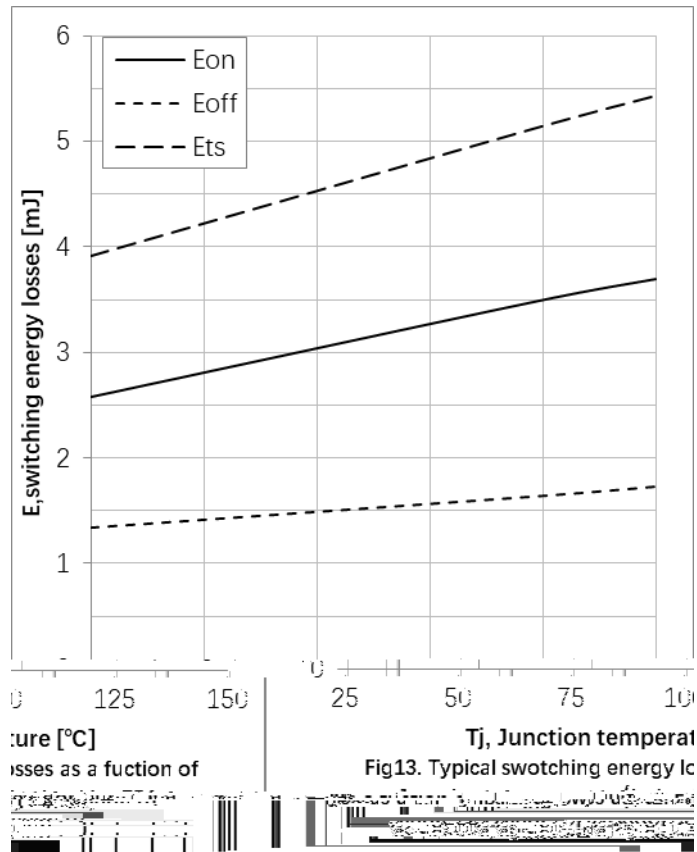
DGW75N65CTL1

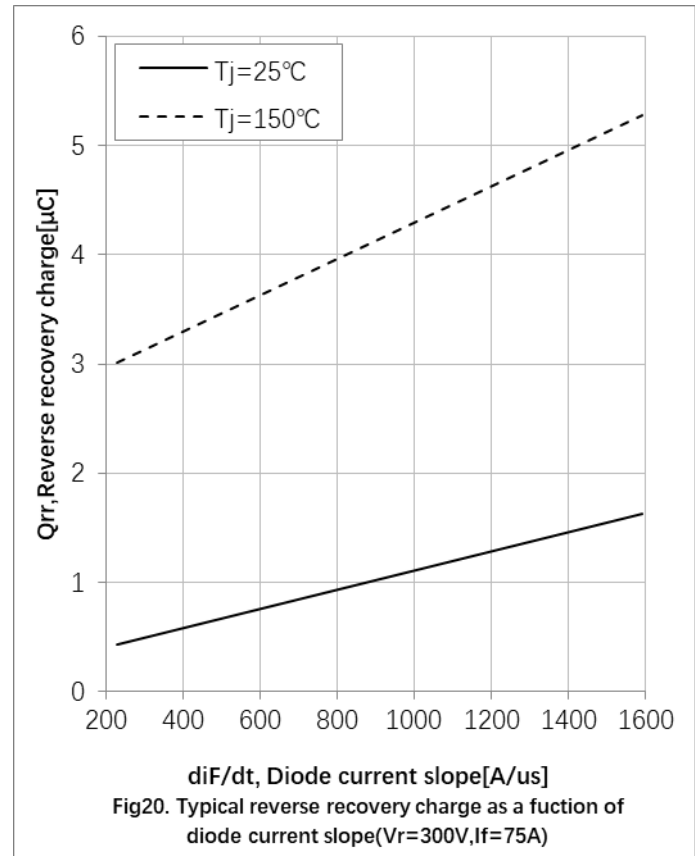
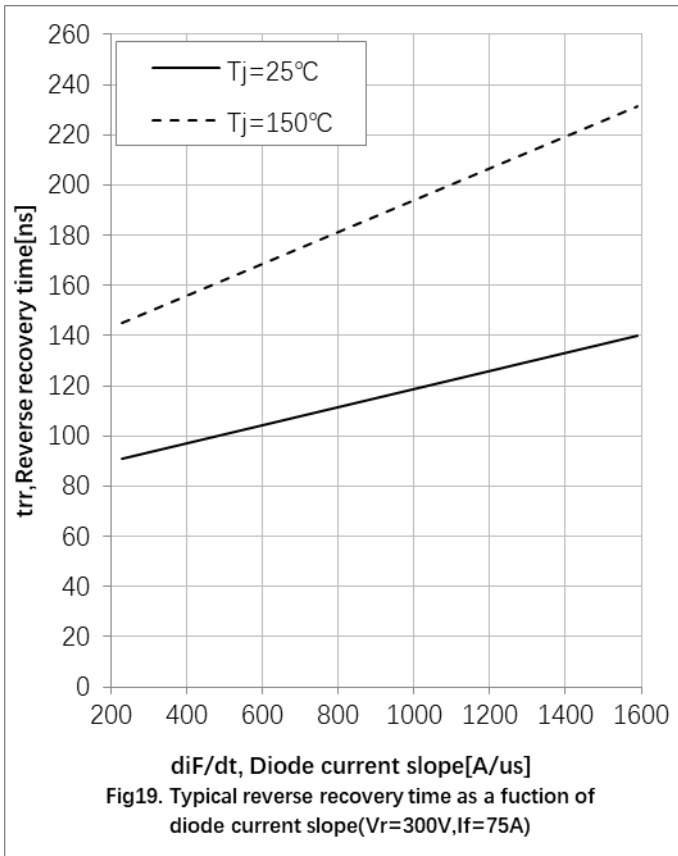
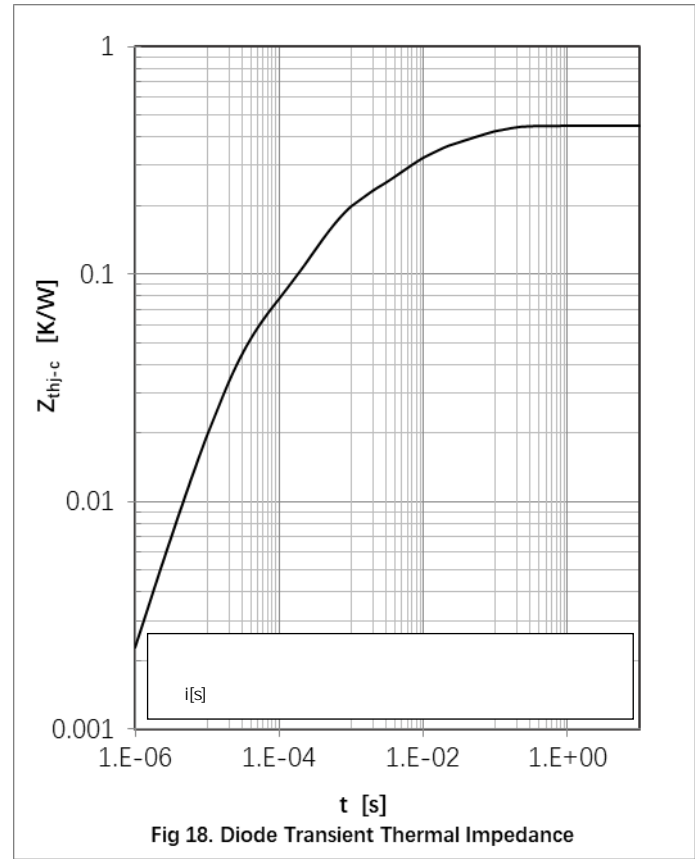
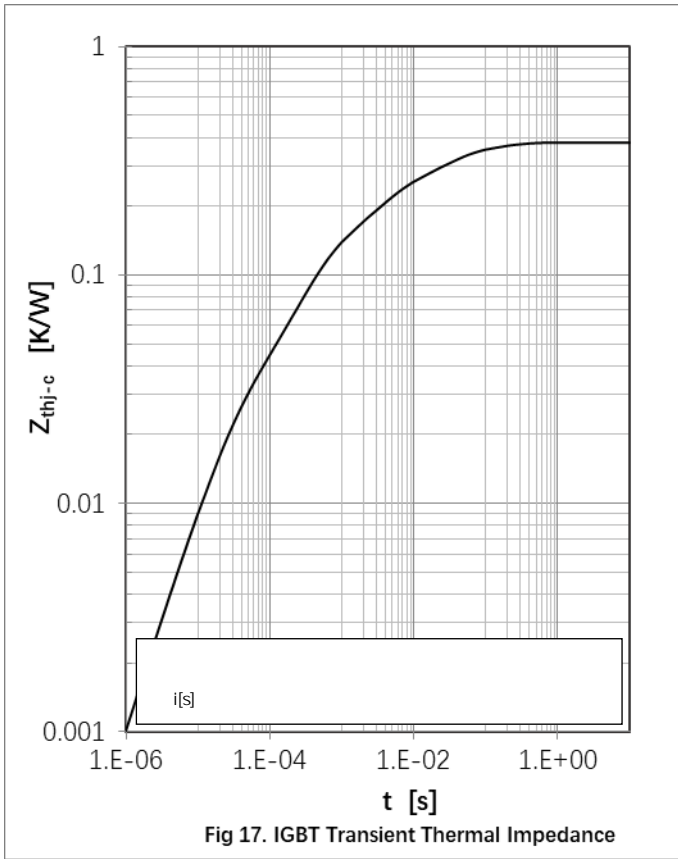
RoHS
COMPLIANT













DGW75N65CTL1

RoHS
COMPLIANT

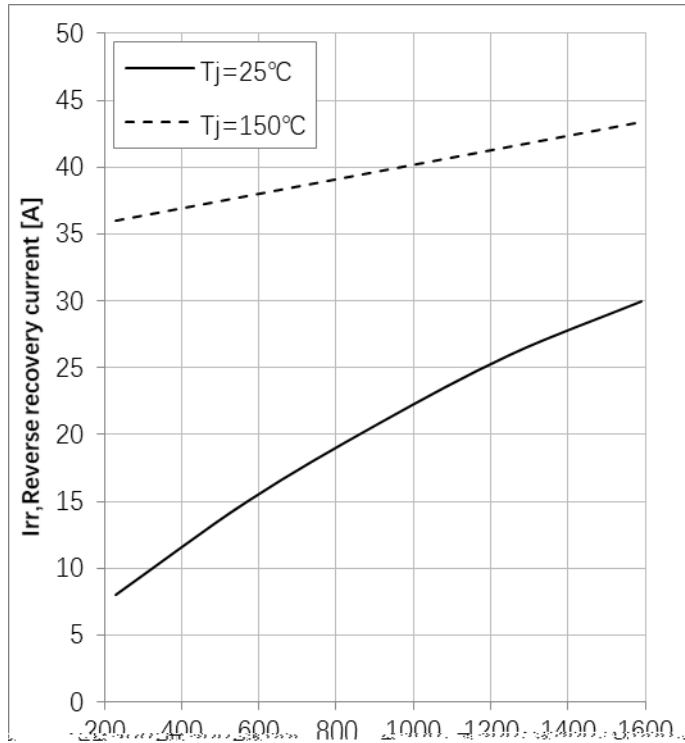


Fig21. Typical reverse recovery current as a function of diode current slope (Vr=300V, If=75A).

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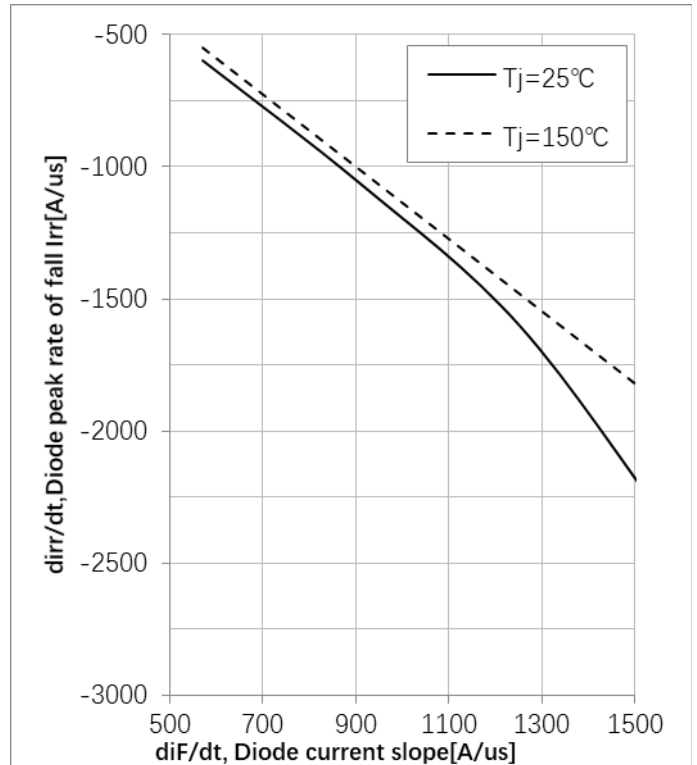


Fig22. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope (Vr=300V, If=75A).

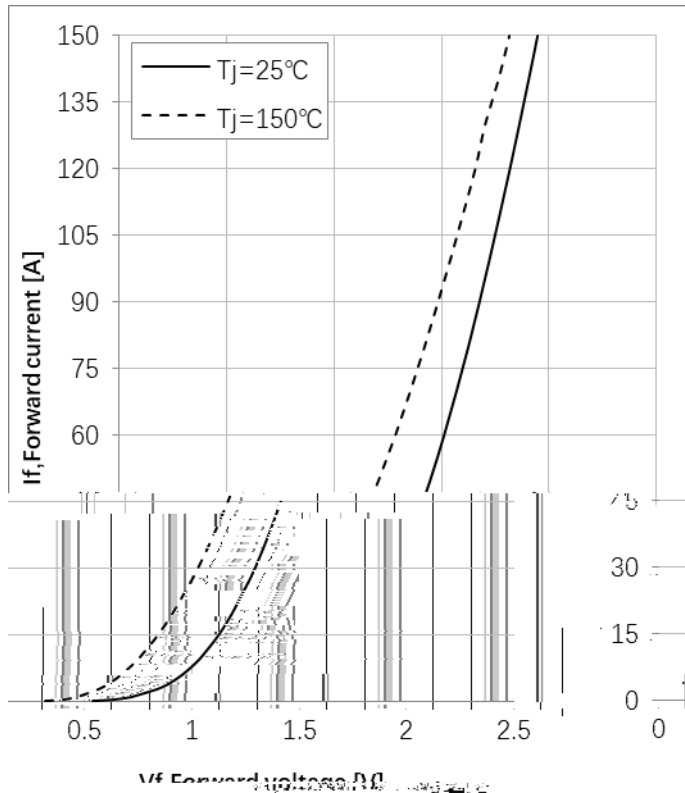


Fig23. Diode forward current as a function of forward voltage.

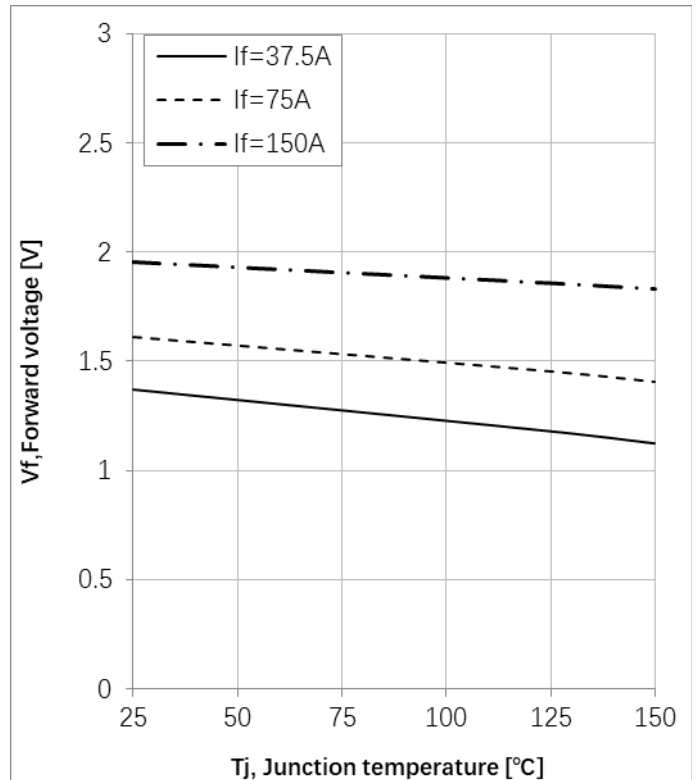


Fig24. Diode forward voltage as a function of junction temperature.

